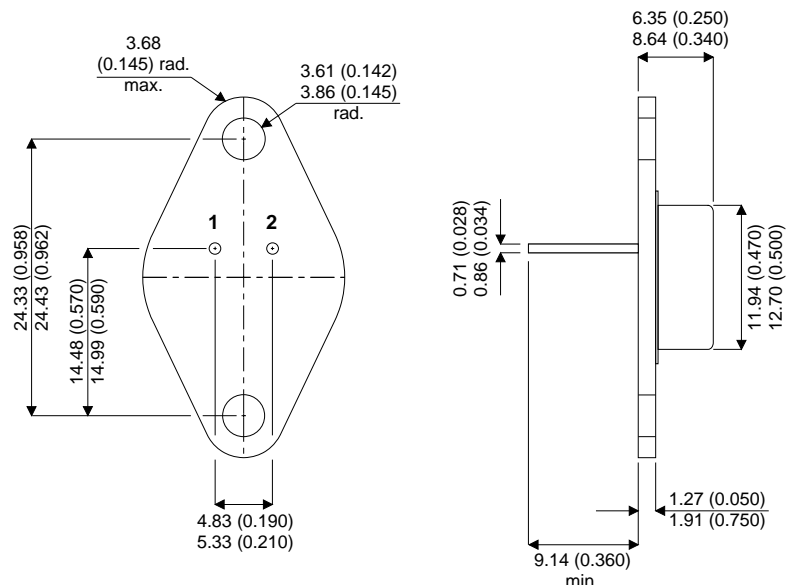


MECHANICAL DATA

Dimensions in mm (inches)

NPN DRIVER TRANSISTOR



TO-66 Metal Package.

Pin 1 – Base Pin 2 – Emitter Case – Collector

- Bipolar Power Transistor
- TO-66 Hermetic Package
- Fast Switching

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

V_{CEO}	Collector – Emitter Voltage	60V
I_C	Continuous Collector Current	3A
P_D	Total Device Dissipation	16W
	Derate above 100°C	6.25°C/W
T_{STG}, T_J	Storage and Operating Junction Temperature Range	-55 to +200°C

Parameter		Test Conditions		Min.	Typ.	Max.	Units
BV_{CEO}	Collector – Emitter Breakdown Voltage	$I_C = 50\text{mA}$		60			V
BV_{EBO}	Emitter – Base Breakdown Voltage	$I_E = 100\mu\text{A}$		7			
BV_{CBO}	Collector – Base Breakdown Voltage	$I_C = 100\mu\text{A}$		60			
I_{CEO}	Collector Cut-off Current	$V_{CE} = 60\text{V}$				20	μA
I_{EBO}	Emitter Cut-off Current	$V_{EB} = 6\text{V}$				5	
I_{CES}	Emitter Cut-off Current	$V_{CE} = 60\text{V}$				20	
H_{FE1}	Current Gain	$V_{CE} = 10\text{V}$	$I_C = 0.5\text{A}$	40		120	—
H_{FE2}	Current Gain	$V_{CE} = 10\text{V}$	$I_C = 0.2\text{A}$	30		120	
h_{fe}	Current Gain	$V_{CE} = 15\text{V}$ $f = 10\text{MHz}$	$I_C = 0.5\text{A}$	3			—
C_{ob}	Output Capacitance	$V_{CB} = 10\text{V}$	$f = 1\text{MHz}$			160	pF
$V_{CEO(sus)}$	Collector – Emitter Saturation Voltage	$I_C = 2\text{A}$	$I_B = 0.2\text{A}$			0.8	V
$V_{BEO(sus)}$	Base – Emitter Saturation Voltage	$I_C = 2\text{A}$	$I_B = 0.2\text{A}$			1.5	
t_{on}	Turn-On Time	$I_C = 1\text{A}$	$I_B = 0.1\text{A}$			500	ns
t_{off}	Turn-Off Time	$I_C = 1\text{A}$	$I_B = 0.1\text{A}$			2.5	μs